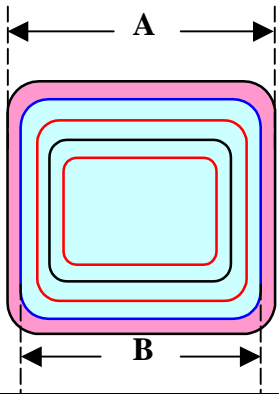


<b>Features :</b>  <ul style="list-style-type: none"> <li>* Extremely low forward volts</li> <li>* Guard ring protection</li> <li>* Low reverse leakage current</li> </ul> 	Chip size(A):	1.270 * 1.270 mm <sup>2</sup>		
	Bond Pad size(B) :	1.143 *1.143 mm <sup>2</sup>		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
<b>Electrical Characteristics</b>	Sym.	Spec. Limit	Unit	
Maximum Instantaneous Forward Volt at IF : 2.0Amp. 25°C	VF max	0.48	Volt	
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	43	Volt.	
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	60	Amp	
Storage Temperature	TSTG	-65 to +125	°C	

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